



Description

The XPX4080FD uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 150 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

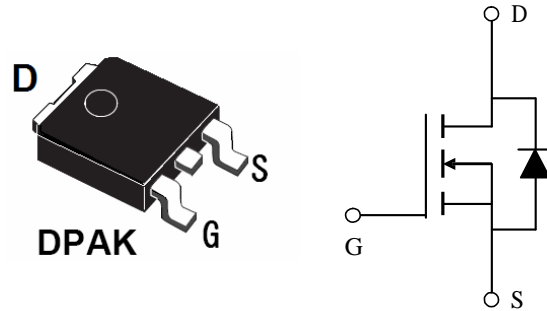
Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

$V_{DS} = 40V, I_D = 80A$

$R_{DS(ON)} = 5.0m\Omega$ (typ) @ $V_{GS} = 10V$

$R_{DS(ON)} = 7.0m\Omega$ (typ) @ $V_{GS} = 4.5V$



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
XPX4080	XPX4080FD	TO-252	-	-	-

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	80	A
Drain Current-Continuous($T_C = 100^\circ C$)	$I_D(100^\circ C)$	48	A
Pulsed Drain Current	I_{DM}	160	A
Maximum Power Dissipation	P_D	60	W
Debating factor		0.57	W/°C
Single pulse avalanche energy ^(Note 5)	E_{AS}	50	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	°C
Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	1.76	°C/W

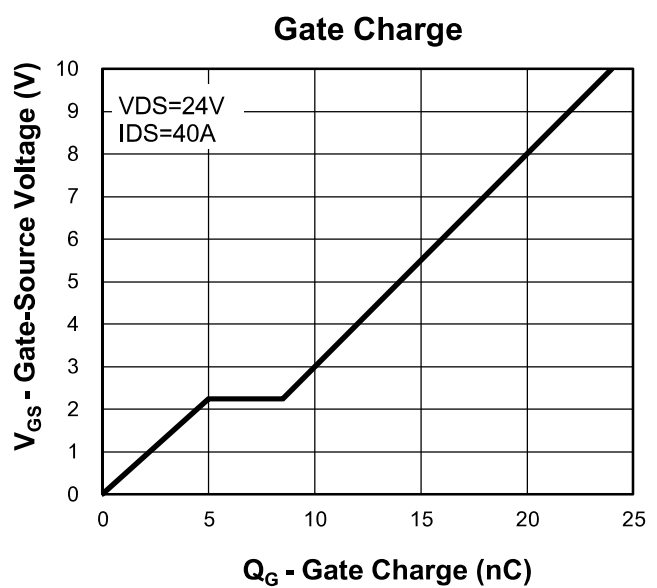
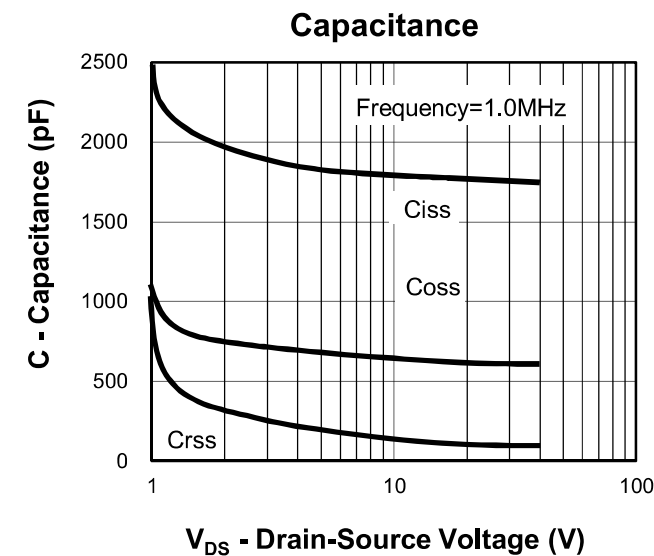
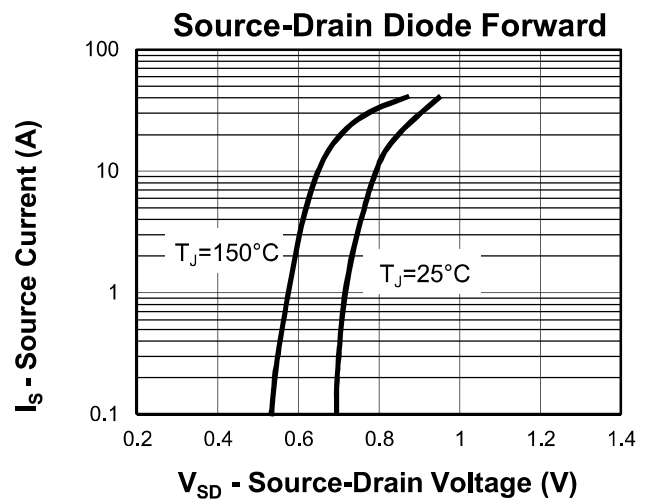
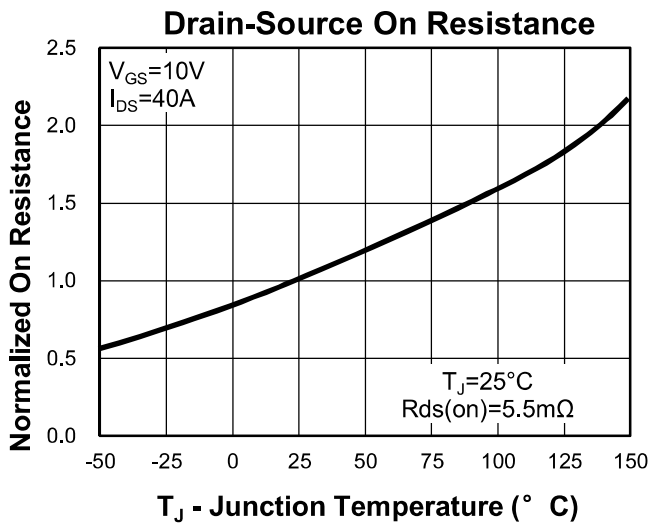
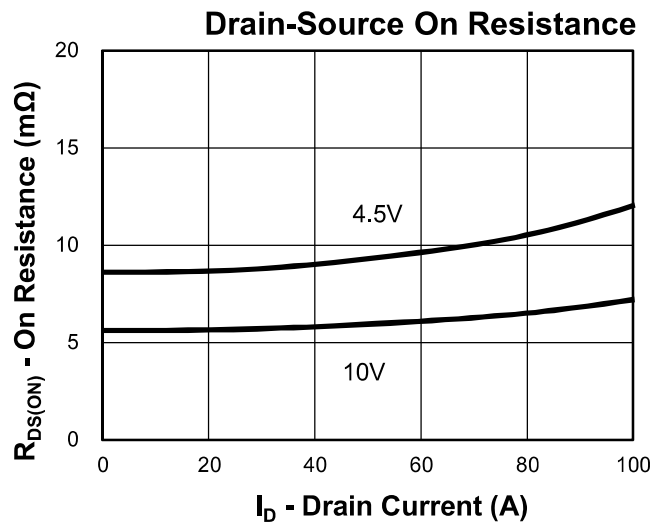
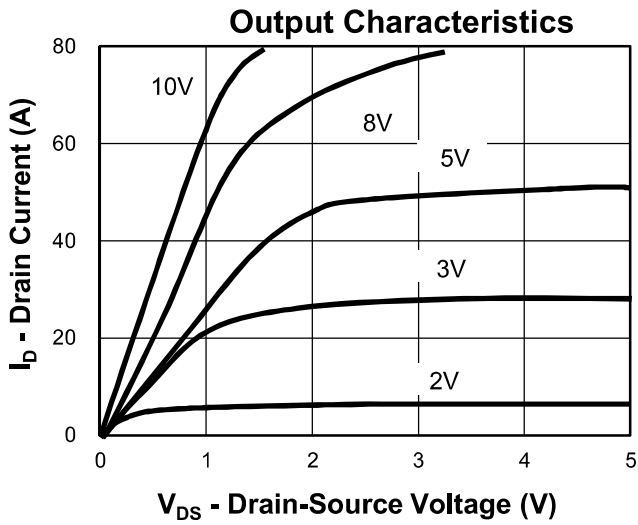
Electrical Characteristics (T_c=25°C unless otherwise noted)

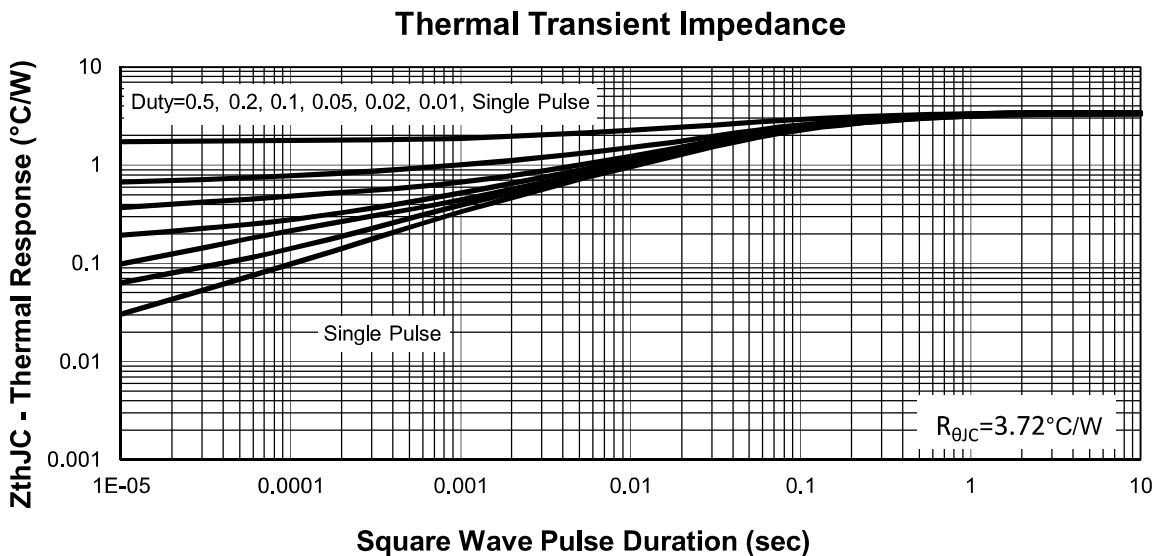
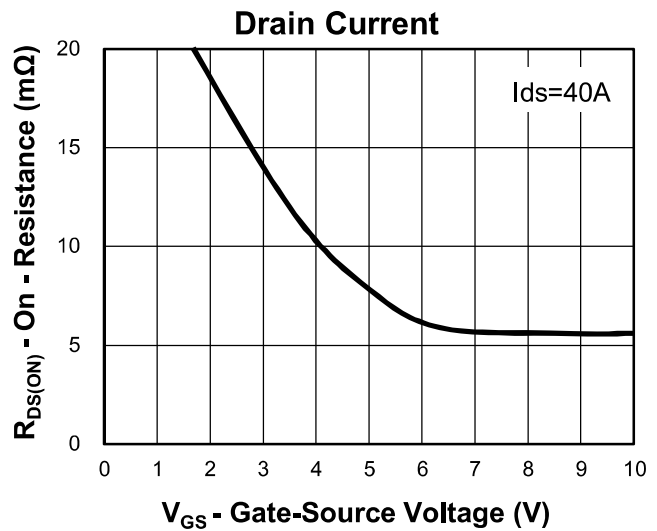
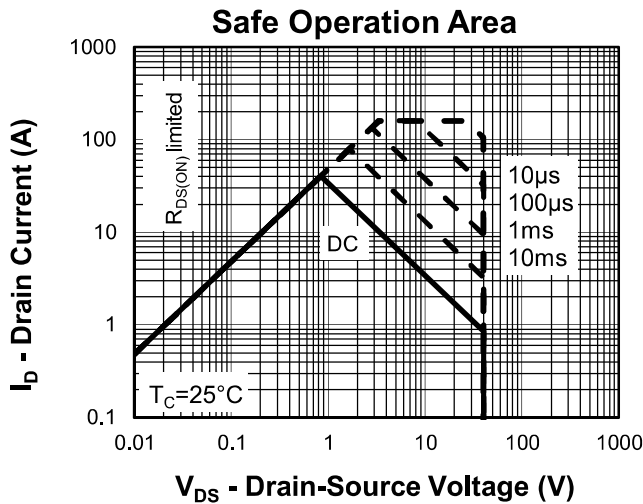
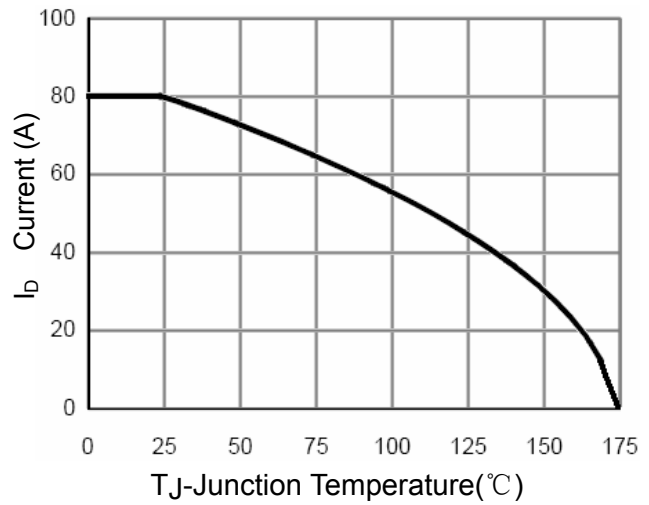
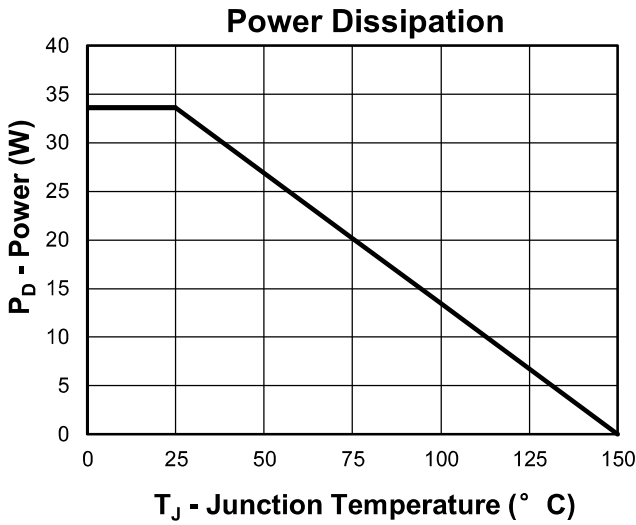
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	40	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1	1.6	2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =30A	-	5.0	7.0	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =20A	30	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, F=1.0MHz	-	1650	-	PF
Output Capacitance	C _{oss}		-	171	-	PF
Reverse Transfer Capacitance	C _{rss}		-	115	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =20V, I _D =20A, R _L =1Ω V _{GS} =10V, R _{GEN} =3Ω	-	5.0	-	nS
Turn-on Rise Time	t _r		-	24	-	nS
Turn-Off Delay Time	t _{d(off)}		-	38	-	nS
Turn-Off Fall Time	t _f		-	12	-	nS
Total Gate Charge	Q _g	V _{DS} =30V, I _D =30A, V _{GS} =10V	-	24	-	nC
Gate-Source Charge	Q _{gs}		-	5.9	-	nC
Gate-Drain Charge	Q _{gd}		-	3.6	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =30A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	48	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =30A di/dt = 100A/μs (Note3)	-	9		nS
Reverse Recovery Charge	Q _{rr}		-	15		nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

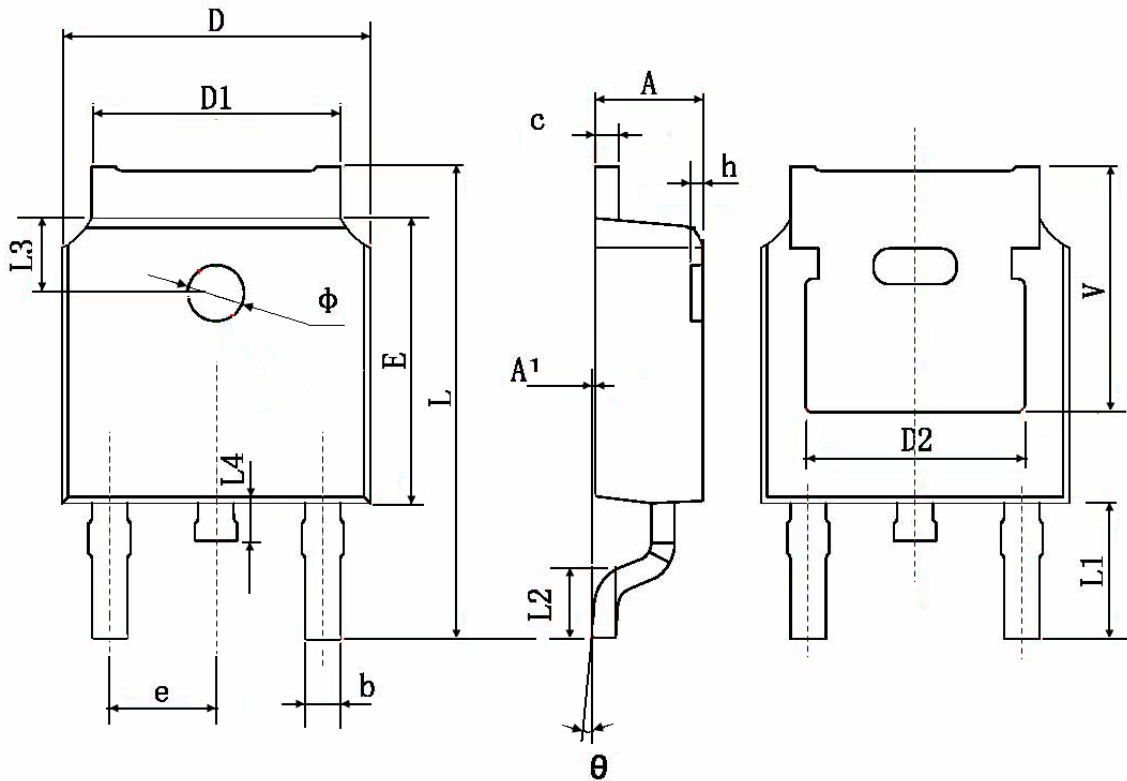
Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. E_{AS} condition: T_J=25°C, V_{DD}=30V, V_G=10V, L=0.5mH, R_g=25Ω

Typical Characteristics





TO-252 Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	

Flow (wave) soldering (solder dipping)

Product	Peak Temperature	Dipping Time
Pb device	245°C ±5°C	5sec±1sec
Pb-Free device	260°C +0/-5°C	5sec±1sec



This integrated circuit can be damaged by ESD. UniverChip Corporation recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedure can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

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